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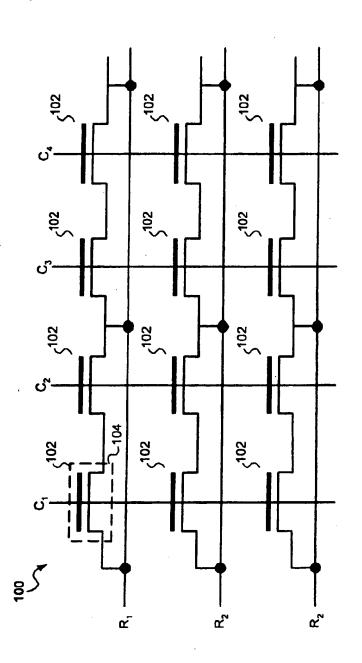


FIGURE 1

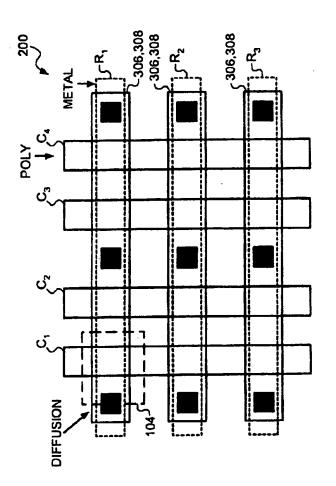


FIGURE 2

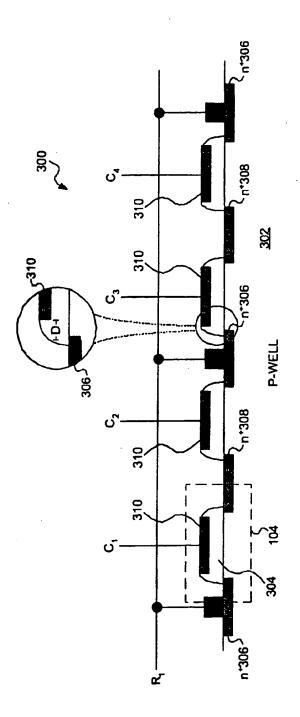


FIGURE 3

-	و و و	\$ 5 5 5 5 7	C0 \$ 7-) 	,		֡֝֝֜֝֓֜֝֓֜֝֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓	ر ح	والم
PROGRAM	YES	ON.	ON	O _N	ISENSE	YES	ON ON	ON ON	ON
(V)	o	8	0	8		0	1.8	0	1.8
(V) VBV	8	8	3.3	3.3		1.8	1.8	0	0
	SC/SR	SC/UR	UC/SR	UC/UR		SC/SR	SC/UR	UC/SR	UC/UR
	PROGRAM					READ			

FIGURE 4

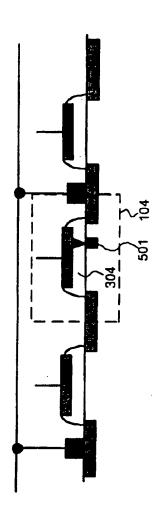
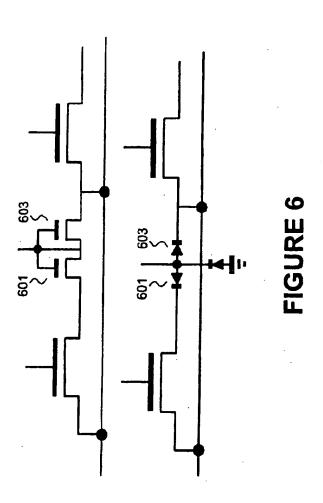


FIGURE 5



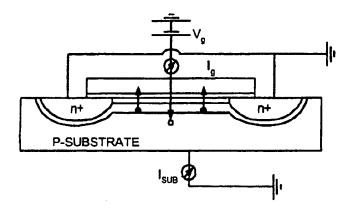


FIGURE 7

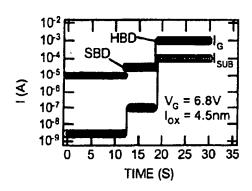


FIGURE 8

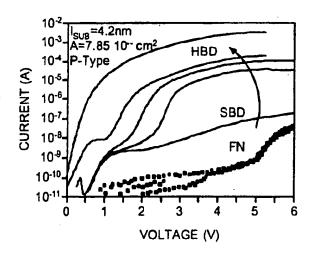


FIGURE 9

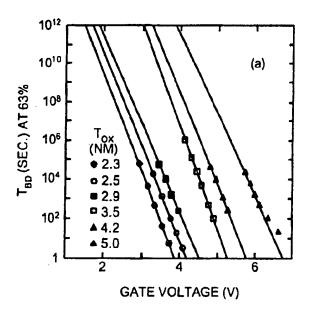


FIGURE 10

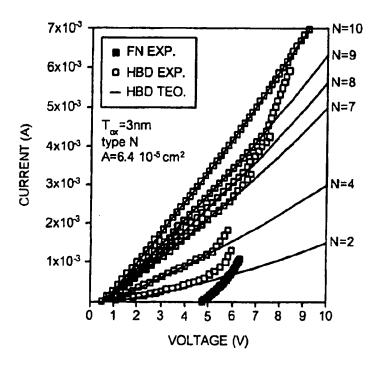
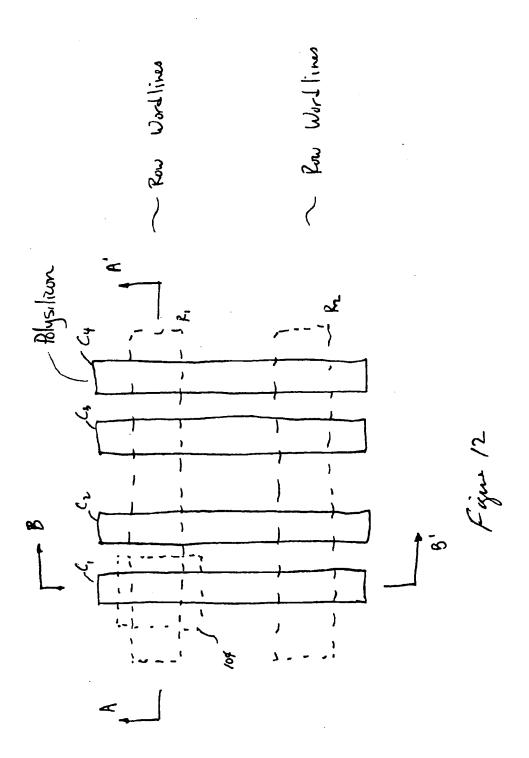
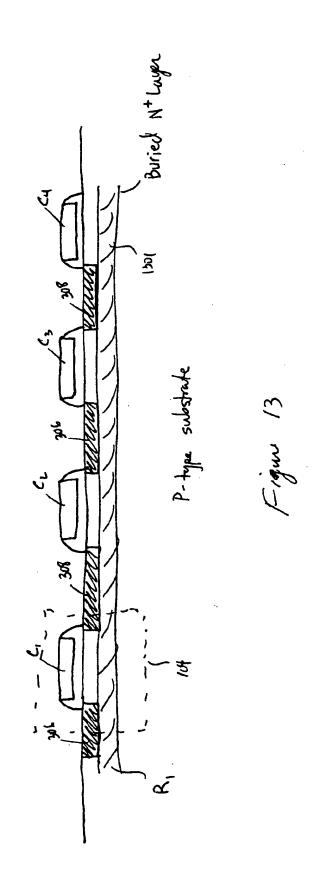
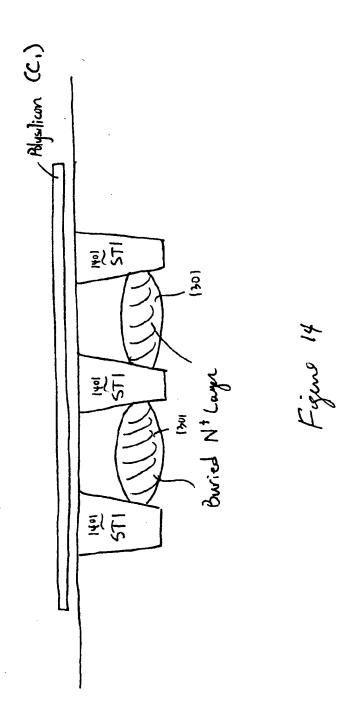


FIGURE 11

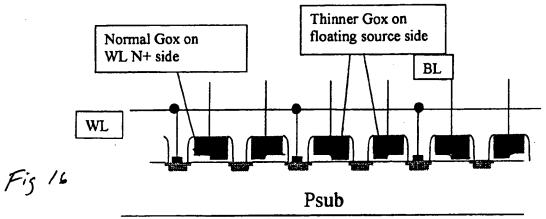


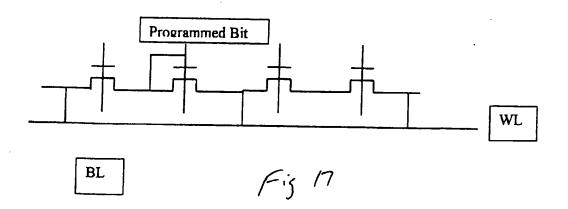




	401 کے	403 کے	405 ك	ر 407		409 ك	411	7 413	7415
PROGRAM	YES	ON	ON	ON	SENSE	YES	S _O	ON N	Q.
VWL (V)	0	Floating	0	Flastins	o	0	Vo or Vc	0	Voo or Vec
VBL (V)	Vap	À.	202	20.5		Voo or Vec	Voo or Ver	O or Flock	0 or Flat
	SC/SR	SC/UR	UC/SR	UC/UR		SC/SR	SC/UR	UC/SR	UC/UR
	PROGRAM					READ			

FIGURE (5





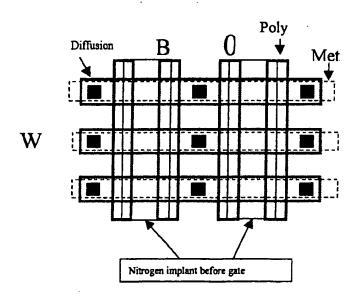
0.18um/0.13um XPM CX cell operation

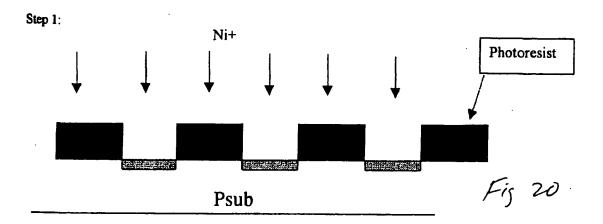
		Vbl (V)	Vwl (V)	Program
Program	SB/SW	Vpp	0	Yes
	SB/UW	Vpp	PC to Vpp/2 and FL	No
	UB/SW	<0.5v	0	No
	UB/UW	<0.5v	PC to Vpp/2 and FL	No
				Isense
Read	SB/SW	Vdd or Vcc	0	Yes
	SB/UW	Vdd or Vcc	Vdd or Vcc	No
	UB/SW	0	0	No
	UB/UW	0	Vdd or Vcc	No

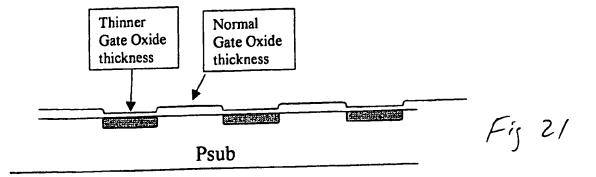
 $Vpp = 8\sim 9V$ for Gox=32A (0.18um) or 5-7 for Gox=20A, or $3\sim 4.5$ V

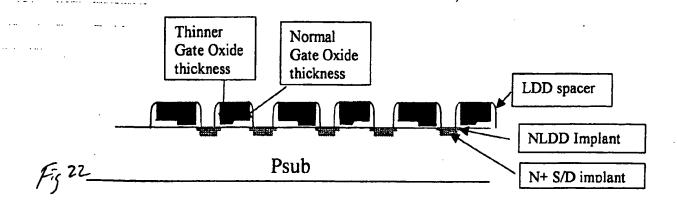
for 10-15A (5 to 10A thinner than normal-standard Gate oxide).

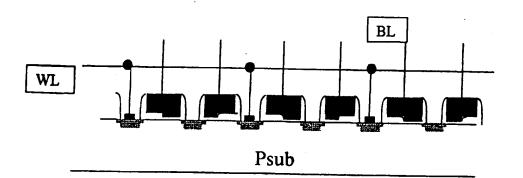
Vdd = I/O Voltage 3.3V or 2.5V Vcc=1.8V for 0.18um and 1.2V for 0.13um











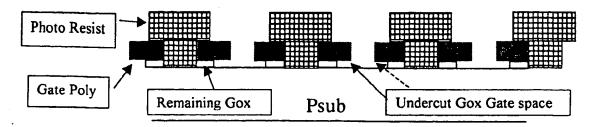
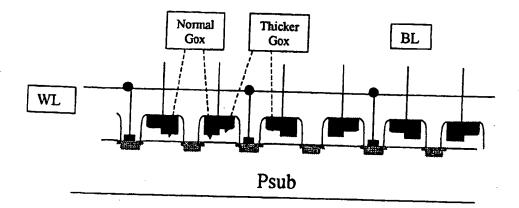
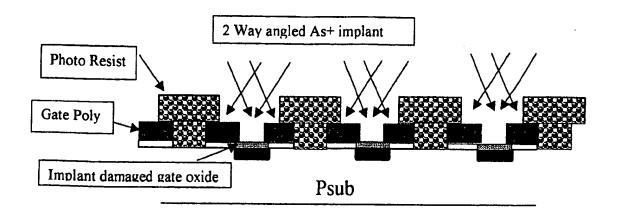
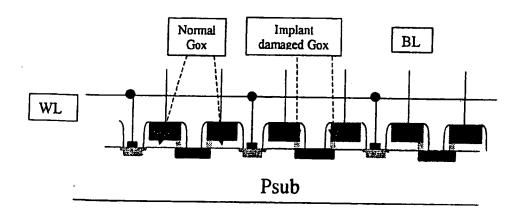
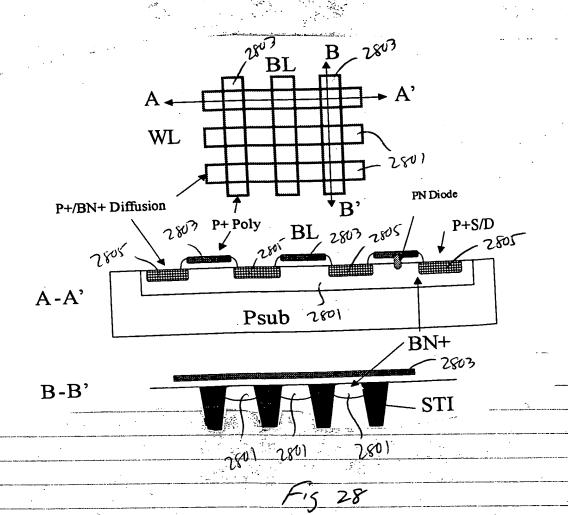


Fig. 24









XPM P+Poly/BN+ 1T cell operation

	<u></u>	Vbl (V)(P+poly)	Vwl (V) (BN+ Diffusion)	Program
Program	SC/SR	Vbp	Vwp	Yes
	SC/UR	Vbp	Floating	No
	UC/SR	<0.5V	Vwp	No
	UC/UR	<0.5V	Floating	No
				Isense
Read	SC/SR	Vrd	0	Yes
	SC/UR	Vrd	Vrd	No
	UC/SR	0	0	No
	UC/UR	0	Vrd	No

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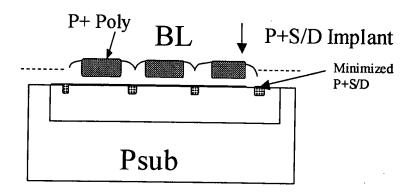
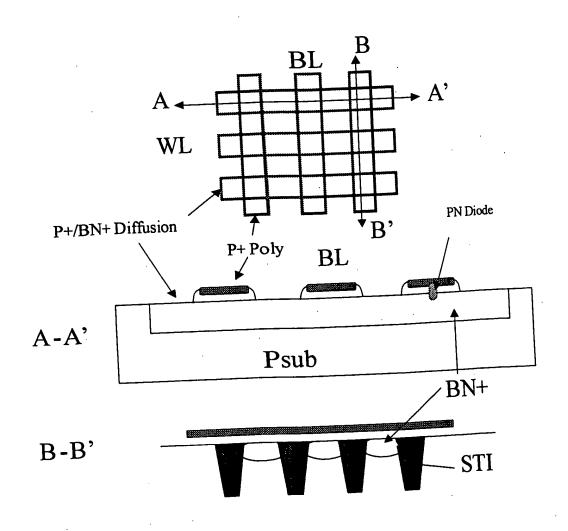
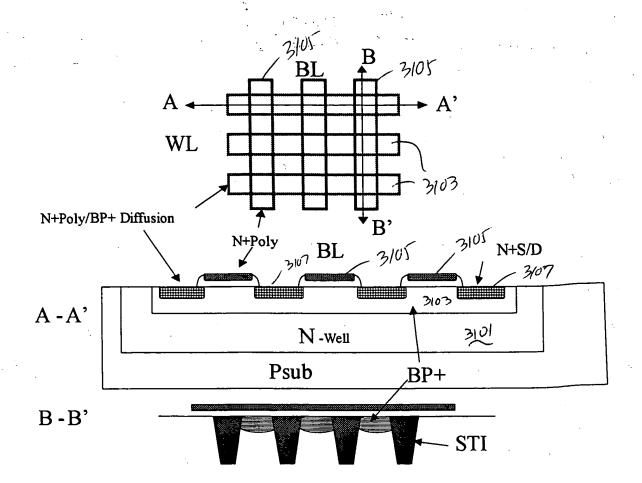


Fig 28 A



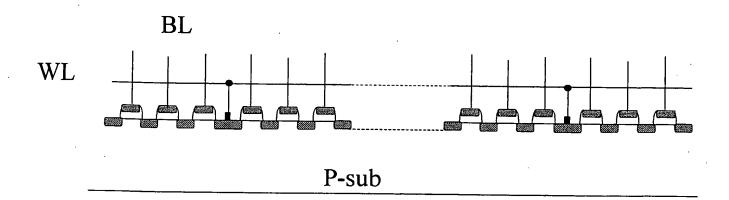


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XPM N+poly/BP+ 1T cell operation

		Vbl (V)(N+poly)	Vwl (V)(BP+)	N-	Program
Program	SC/SR	Vbp	Vwp	Vwp	Yes
	SC/UR	Vbp	Floatin	Vwp	No
	UC/SR	(0 ~ -	Vwp	Vwp	No
	UC/UR	(0 ~ -	Floatin	Vwp	No
					Isense
Read	SC/SR	0	Vrd	Vdd or Vrd	Yes
	SC/UR	0	0	Vdd or Vrd	No
	UC/SR	Vrd	Vrd	Vdd or Vrd	No
	UC/UR	Vrd	0	Vdd or Vrd	No

Fiz 32



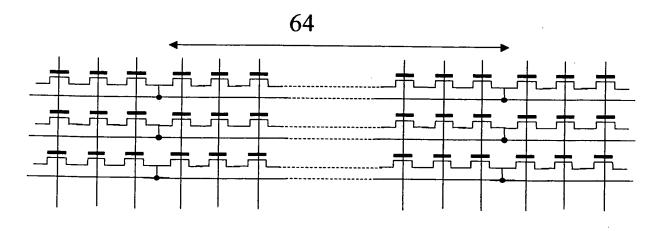


Figure 33